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Poster Presentation

## [AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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10:40 AM - 1:10 PM

## [AMDp1-15]Effect of Fluorine Doping on Illumination Stability of Solution-Processed IGZO TFTs

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Keywords:oxide semiconductor, thin-film transistors, fluorine, a-IGZO, passivation

This study investigated the effect of F doping though NBIS comparison between F-doped and conventional IGZO TFTs. The oxygen vacancies in the IGZO layer were reduced and the bandgap of the IGZO was widened by F doping. As a result of this, the illumination stability of F doped-TFTs was improved.